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December 2013

FQP2N90

N-Channel QFET® MOSFET

900 V, 2.2 A, 7.2 Ω

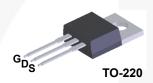
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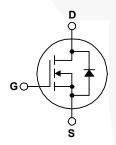
This N-Channel enhancement mode power MOSFET is • 2.2 A, 900 V, $R_{DS(on)}$ = 7.2 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state

Low Gate Charge (Typ. 12 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 5.5 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_D = 1.1 A$





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP2N90	Unit	
V _{DSS}	Drain-Source Voltage		900	V	
I _D	Drain Current - Continuous (T _C = 25°C)		2.2	А	
	- Continuous (T _C = 100°C)		1.39	Α	
I _{DM}	Drain Current - Pulsed	Note 1)	8.8	А	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	Note 2)	170	mJ	
I _{AR}	Avalanche Current	Note 1)	2.2	Α	
E _{AR}	Repetitive Avalanche Energy (Note		8.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.0	V/ns	
P_{D}	Power Dissipation (T _C = 25°C)		85	W	
	- Derate above 25°C		0.68	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		300	°C	

Thermal Characteristics

Symbol	Parameter	FQP2N90	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.47	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP2N90	FQP2N90	TO-220	Tube	N/A	N/A	50 units

Symbol	Parameter Test Conditions		Min.	Тур.	Max.	Uni
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	900			V
ΔBV _{DSS} / ΔT	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	1	1.0		V/°C
I _{DSS}	7 Cata Valta as Dusin Commant	V _{DS} = 900 V, V _{GS} = 0 V			10	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 720 V, T _C = 125°C	-		100	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	-		100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	1		-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 1.1 A		5.6	7.2	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 1.1 A		2.0		S
Dynam C _{iss}	ic Characteristics Input Capacitance	I		390	500	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		45	60	рF
C _{rss}	Reverse Transfer Capacitance			5.5	7.0	рF
Switch	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 450 V, I _D = 2.2 A,		15	40	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		35	80	ns
t _{d(off)}	Turn-Off Delay Time			20	50	ns
t _f	Turn-Off Fall Time	(Note 4)		30	70	ns
Q_g	Total Gate Charge	$V_{DS} = 720 \text{ V}, I_D = 2.2 \text{ A},$		12	15	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V (Note 4)		2.8		nC
Q _{gd}	Gate-Drain Charge			6.1		nC
Drain-S	Source Diode Characteristics ar	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				2.2	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				8.8	Α

I _S	Maximum Continuous Drain-Source Diode Forward Current				2.2	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				8.8	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.2 A			1.4	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 V, I_{S} = 2.2 A,$		400		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		1.6	//	μС

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 65 mH, I $_{AS}$ = 2.2 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.
- 3. I $_{SD} \le$ 2.2 A, di/dt \le 200 A/µs , V $_{DD} \le$ BV $_{DSS,}$ starting $\,$ T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature.

Typical Characteristics

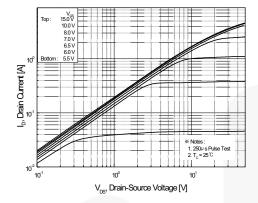


Figure 1. On-Region Characteristics

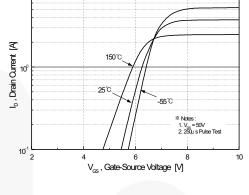


Figure 2. Transfer Characteristics

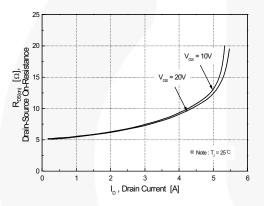


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

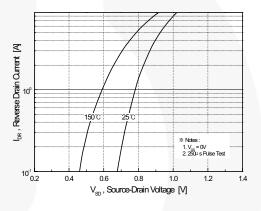


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

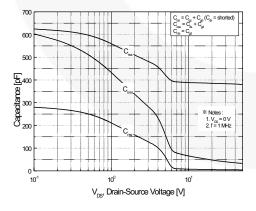


Figure 5. Capacitance Characteristics

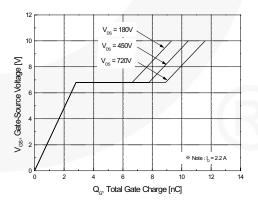
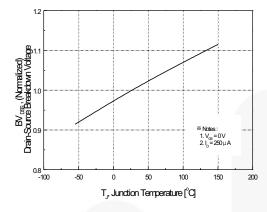


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

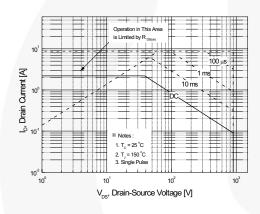


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Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



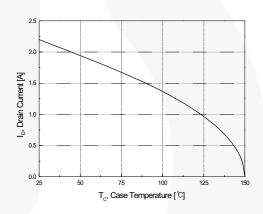


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

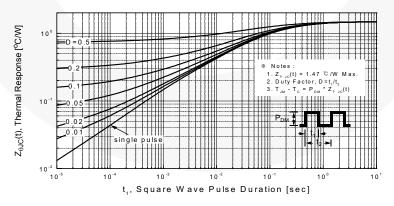


Figure 11. Transient Thermal Response Curve

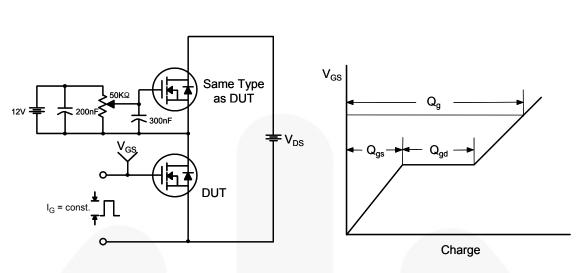


Figure 12. Gate Charge Test Circuit & Waveform

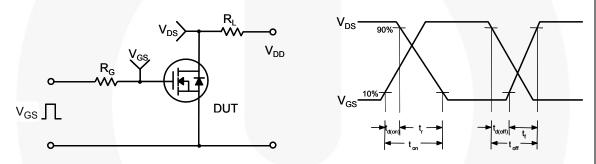


Figure 13. Resistive Switching Test Circuit & Waveforms

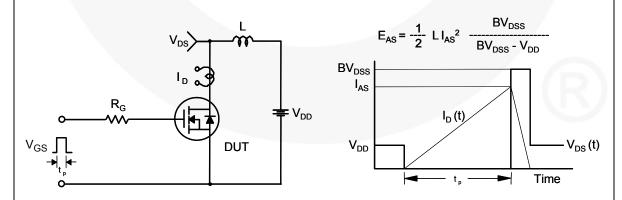
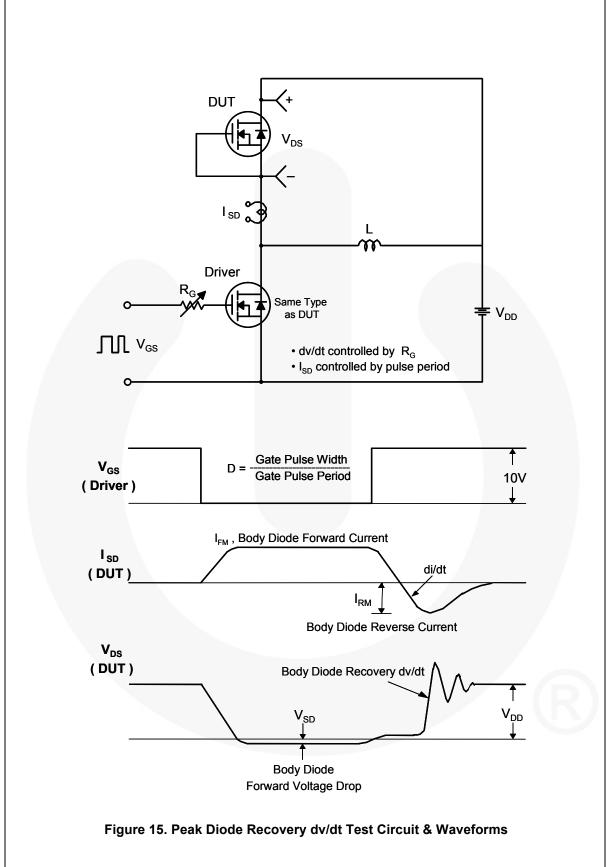


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

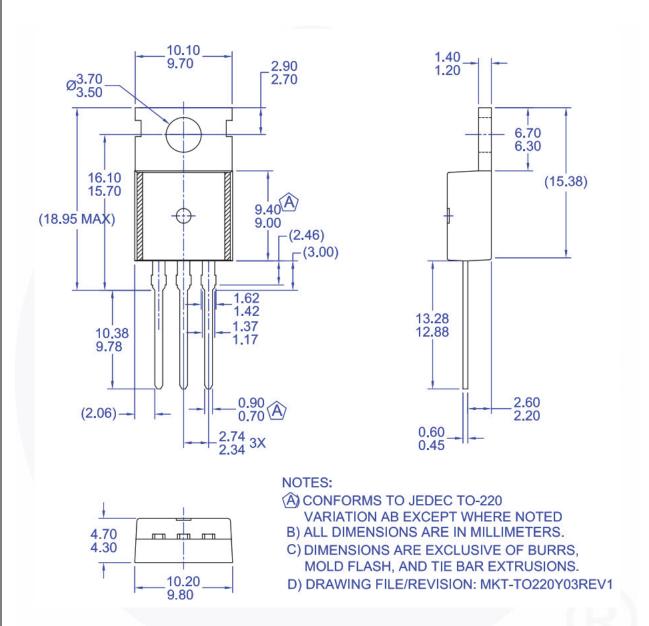


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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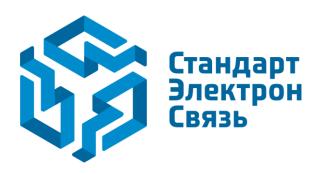
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